SONY

CXK5T16100TM -12LLX

65536-word × 16-bit High Speed CMOS Static RAM *Preliminary*

For the availability of this product, please contact the sales office.

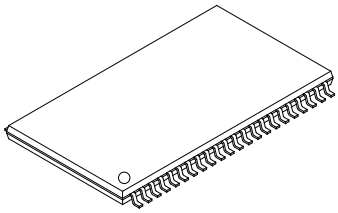
Description

The CXK5T16100TM is a general purpose high speed CMOS static RAM organized as 65536-words by 16-bits.

Special feature are low power consumption and high speed.

The CXK5T16100TM is a suitable RAM for portable equipment with battery back up.

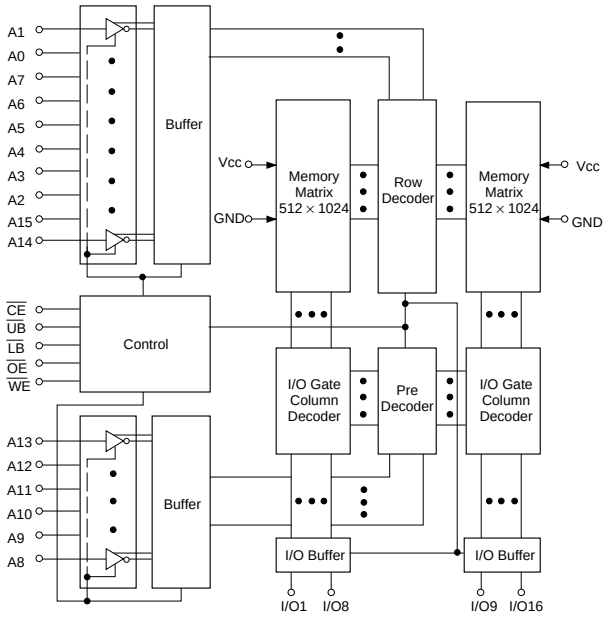
44 pin TSOP (PIastic)



Features

- Extended operating temperature range: –25 to +85°C
- Wide supply voltage range operation: 2.7 to 3.6V
- Fast access time: (Access time)
  - 3.0V operation 120ns (max.)
  - 3.3V operation 100ns (max.)
- Low power consumption operation:
  - Standby / DC operation
  - 1.6µW (typ.) / 3.3mW (typ.)
  - 100µW (max.) / 11mW (max.)
- Fully static memory … No clock or timing strobe required
- Equal access and cycle time
- Common data input and output: three state output
- Directly LVTTL compatible: All inputs and outputs
- Low voltage data retention: 2.0V (min.)
- 400mil 44pin TSOP (type II) package

Block Diagram



Function

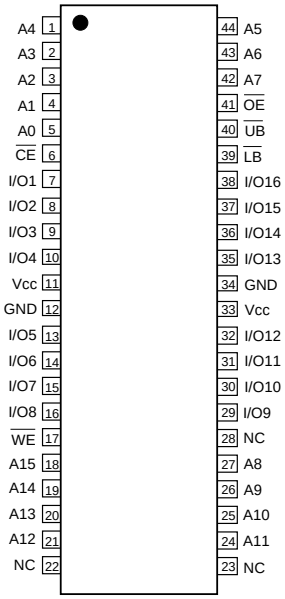
65536-word x 16-bit static RAM

Structure

Silicon gate CMOS IC

PE96405-ST

Pin Configuration (Top View)



Pin Description

Symbol	Description
A0 to A15	Address input
I/O1 to I/O16	Data input/output
$\overline{CE}$	Chip enable input
$\overline{LB}$	Byte enable input (I/O1 to I/O8)
$\overline{UB}$	Byte enable input (I/O9 to I/O16)
$\overline{WE}$	Write enable input
$\overline{OE}$	Output enable input
V_{CC}	Power supply
GND	Ground
NC	No connection

Absolute Maximum Ratings (Ta = 25°C, GND = 0V)

Item	Symbol	Rating	Unit
Supply voltage	V_{CC}	–0.5 to +4.6	V
Input voltage	V_{IN}	–0.5*1 to V_{CC} + 0.5	V
Input and output voltage	$V_{I/O}$	–0.5*1 to V_{CC} + 0.5	V
Allowable power dissipation	P_D	0.7	W
Operating temperature	Topr	–25 to +85	°C
Storage temperature	Tstg	–55 to +150	°C
Soldering temperature · time	Tsolder	235 · 10	°C · s

*1 V_{IN}, $V_{I/O}$ = –3.0V Min. for pulse width less than 50ns.

Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O1 to I/O8	I/O9 to I/O16	Vcc Current
H	×	×	×	×	Not selected	Not selected	I_{SB1}, I_{SB2}
L	L	H	L	L	Read	Read	I_{CC1}, I_{CC2}, I_{CC3}
			L	H	Read	High-Z	I_{CC1}, I_{CC2}, I_{CC3}
			H	L	High-Z	Read	I_{CC1}, I_{CC2}, I_{CC3}
L	×	L	L	L	Write	Write	I_{CC1}, I_{CC2}, I_{CC3}
			L	H	Write	Not Write/Hi-Z	I_{CC1}, I_{CC2}, I_{CC3}
			H	L	Not Write/Hi-Z	Write	I_{CC1}, I_{CC2}, I_{CC3}
L	H	H	×	×	High-Z	High-Z	I_{CC1}, I_{CC2}, I_{CC3}
L	×	×	H	H	High-Z	High-Z	I_{CC1}, I_{CC2}, I_{CC3}

×: “H” or “L”

DC Recommended Operating Conditions (Ta = –25 to +85°C, GND = 0V)

Item	Symbol	V_{CC} = 2.7 to 3.6V			V_{CC} = 3.3V ± 0.3V			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
Supply voltage	V_{CC}	2.7	3.3	3.6	3.0	3.3	3.6	V
Input high voltage	V_{IH}	2.4	—	V_{CC} + 0.3	2.0	—	V_{CC} + 0.3	
Input low voltage	V_{IL}	–0.3*1	—	0.4	–0.3*1	—	0.8	

*1 V_{IL}=–3.0V Min. for pulse width less than 50ns.

Electrical Characteristics

DC and operating characteristics (V_{CC} = 2.7 to 3.6V, GND = 0V, Ta = –25 to +85°C)

Item	Symbol	Test condition		Min.	Typ.*2	Max.	Unit
Input leakage current	I_{LI}	V_{IN} = GND to V_{CC}		–1	—	1	µA
Output leakage current	I_{LO}	$\overline{CE}$ = V_{IH} or $\overline{UB}$ = V_{IH} or $\overline{LB}$ = V_{IH} or $\overline{OE}$ = V_{IH} or $\overline{WE}$ = V_{IL} $V_{I/O}$ = GND to V_{CC}		–1	—	1	µA
Operating power supply current	I_{CC1}	$\overline{CE}$ = V_{IL} V_{IN} = V_{IH} or V_{IL} I_{OUT} = 0mA		—	1	3	mA
Average operating current	I_{CC2}	Min. cycle Duty = 100% I_{OUT} = 0mA		—	35	50	mA
	I_{CC3}	Cycle time 1µs Duty = 100% I_{OUT} = 0mA $\overline{CE}$ ≤ 0.2V V_{IL} ≤ 0.2V V_{IH} ≥ V_{CC} – 0.2V		—	10	20	mA
Standby current	I_{SB1}	$\overline{CE}$ ≥ V_{CC} – 0.2V	–25 to +85°C	—	—	28	µA
			–25 to +70°C	—	—	14	
			+25°C	—	0.48	—	
	I_{SB2}	$\overline{CE}$ = V_{IH}		—	0.03	0.6	mA
Output high voltage	V_{OH}	I_{OH} = –2.0mA		2.4	—	—	V
Output low voltage	V_{OL}	I_{OL} = 2.0mA		—	—	0.4	V

*2 V_{CC} = 3.3V, Ta = 25°C

I/O capacitance (Ta = 25°C, f = 1MHz)

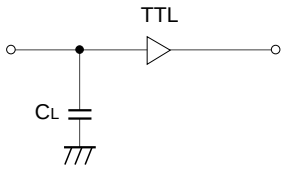
Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{IN}	V_{IN} = 0V	—	—	8	pF
I/O capacitance	$C_{I/O}$	$V_{I/O}$ = 0V	—	—	10	pF

Note) This parameter is sampled and is not 100% tested.

AC Characteristics

• **AC test conditions** (Ta = –25 to +85°C)

Item	Conditions	
	V_{CC} = 2.7 to 3.6V	V_{CC} = 3.3V ± 0.3V
Input pulse high level	V_{IH} = 2.4V	V_{IH} = 2.2V
Input pulse low level	V_{IL} = 0.4V	V_{IL} = 0.6V
Input rise time	t_r = 5ns	t_r = 5ns
Input fall time	t_f = 5ns	t_f = 5ns
Input and output reference level	1.4V	1.4V
Output load conditions	C_L*1 = 100pF, 1TTL	C_L*1 = 100pF, 1TTL



*1 C_L includes scope and jig capacitances.

• **Read cycle** ($\overline{WE}$ = "H")

Item	Symbol	V_{CC} = 2.7 to 3.6V		V_{CC} = 3.3V ± 0.3V		Unit
		Min.	Max.	Min.	Max.	
Read cycle time	t_{RC}	120	—	100	—	ns
Address access time	t_{AA}	—	120	—	100	ns
Chip enable access time ($\overline{CE}$)	t_{CO}	—	120	—	100	ns
Byte enable access time ($\overline{UB}$, $\overline{LB}$)	t_{BO}	—	60	—	50	ns
Output enable to output valid	t_{OE}	—	60	—	50	ns
Output hold from address change	t_{OH}	10	—	10	—	ns
Chip enable to output in low Z ($\overline{CE}$)	t_{LZ}	10	—	10	—	ns
Output enable to output in low Z ($\overline{OE}$)	t_{OLZ}	5	—	5	—	ns
Byte enable to output in low Z ($\overline{UB}$, $\overline{LB}$)	t_{BLZ}	5	—	5	—	ns
Chip disable to output in high Z ($\overline{CE}$)	t_{HZ}*1	—	40	—	40	ns
Chip disable to output in high Z ($\overline{OE}$)	t_{OHZ}*1	—	35	—	35	ns
Byte disable to output in high Z ($\overline{UB}$, $\overline{LB}$)	t_{BHZ}*1	—	35	—	35	ns

*1 t_{HZ}, t_{OHZ} and t_{BHZ} are defined as the time required for outputs to turn to high impedance state and are not referred to as output voltage levels.

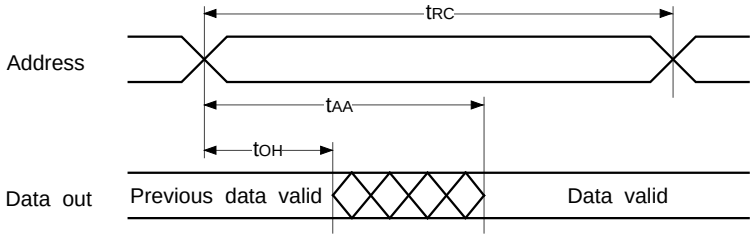
• **Write cycle**

Item	Symbol	V_{CC} = 2.7 to 3.6V		V_{CC} = 3.3V ± 0.3V		Unit
		Min.	Max.	Min.	Max.	
Write cycle time	t_{WC}	120	—	100	—	ns
Address valid to end of write	t_{AW}	100	—	80	—	ns
Chip enable to end of write	t_{CW}	100	—	80	—	ns
Byte enable to end of write	t_{BW}	100	—	80	—	ns
Data to write time overlap	t_{DW}	50	—	40	—	ns
Data hold from write time	t_{DH}	0	—	0	—	ns
Write pulse width	t_{WP}	70	—	70	—	ns
Address setup time	t_{AS}	0	—	0	—	ns
Write recovery time ($\overline{WE}$)	t_{WR}	5	—	5	—	ns
Write recovery time ($\overline{CE}$, $\overline{UB}$, $\overline{LB}$)	t_{WR1}	5	—	5	—	ns
Output active from end of write	t_{OW}	5	—	5	—	ns
Write to output in high Z	t_{WHZ}*2	—	40	—	40	ns

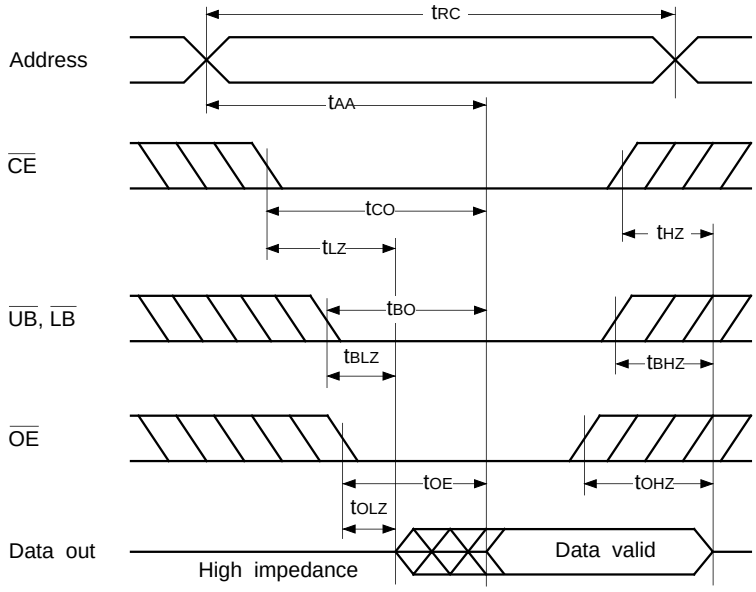
*2 t_{WHZ} is defined as the time required for outputs to turn to high impedance state and is not referred to as output voltage levels.

Timing Waveform

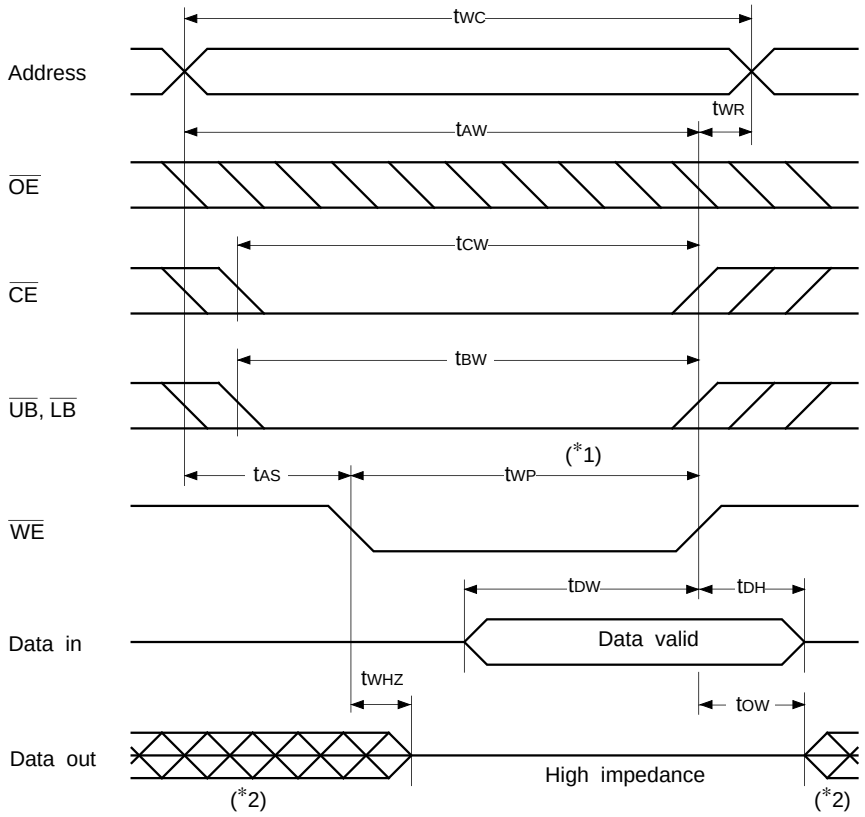
• Read cycle (1) : $\overline{CE}$ = $\overline{OE}$ = V_{IL}, $\overline{WE}$ = V_{IH}, $\overline{UB}$ and, or $\overline{LB}$ = V_{IL}



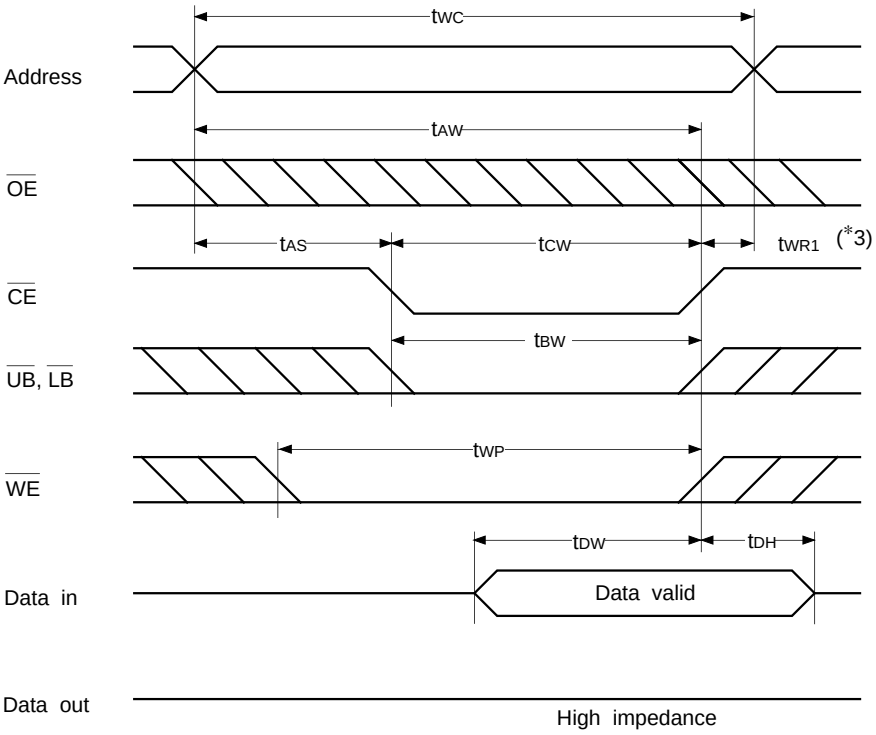
• Read cycle (2) : $\overline{WE}$ = V_{IH}



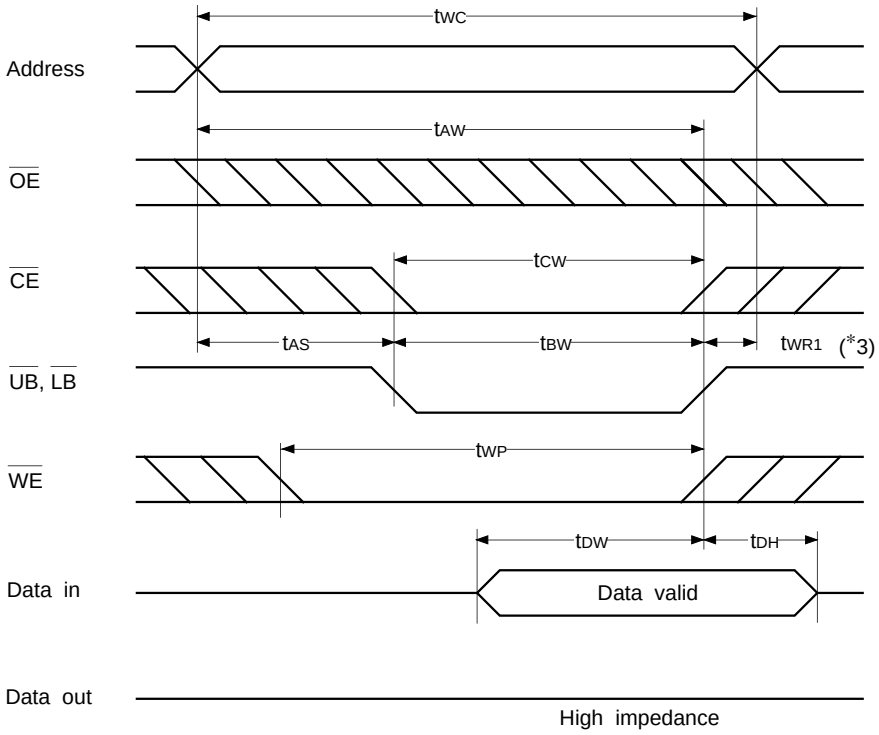
• Write cycle (1) : $\overline{WE}$ control



• Write cycle (2) : $\overline{CE}$ control



• Write cycle (3) : $\overline{UB}$, $\overline{LB}$ control



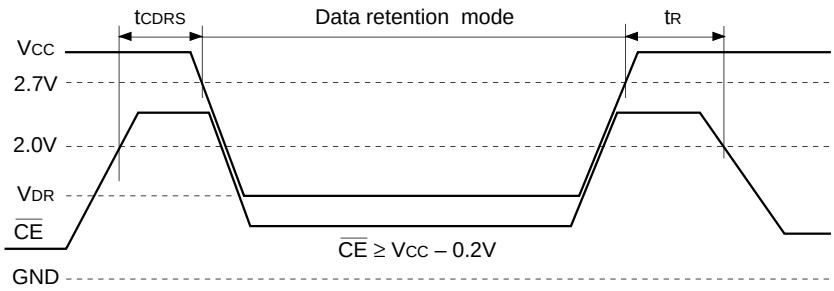
*1 Write is executed when all of the $\overline{CE}$, $\overline{WE}$ and ($\overline{UB}$ and, or $\overline{LB}$) are at low simultaneously.

*2 Do not apply the data input voltage of the opposite phase to the output while I/O pin is in output condition.

*3 t_{WR1} (for I/O1 to 8) is tested from either the rising edge of $\overline{CE}$ or $\overline{LB}$, whichever comes earlier, until the end of the write cycle.
t_{WR1} (for I/O9 to 16) is tested from either the rising edge of $\overline{CE}$ or $\overline{UB}$, whichever comes earlier, until the end of the write cycle.

Data Retention Waveform

• Low supply voltage data retention waveform



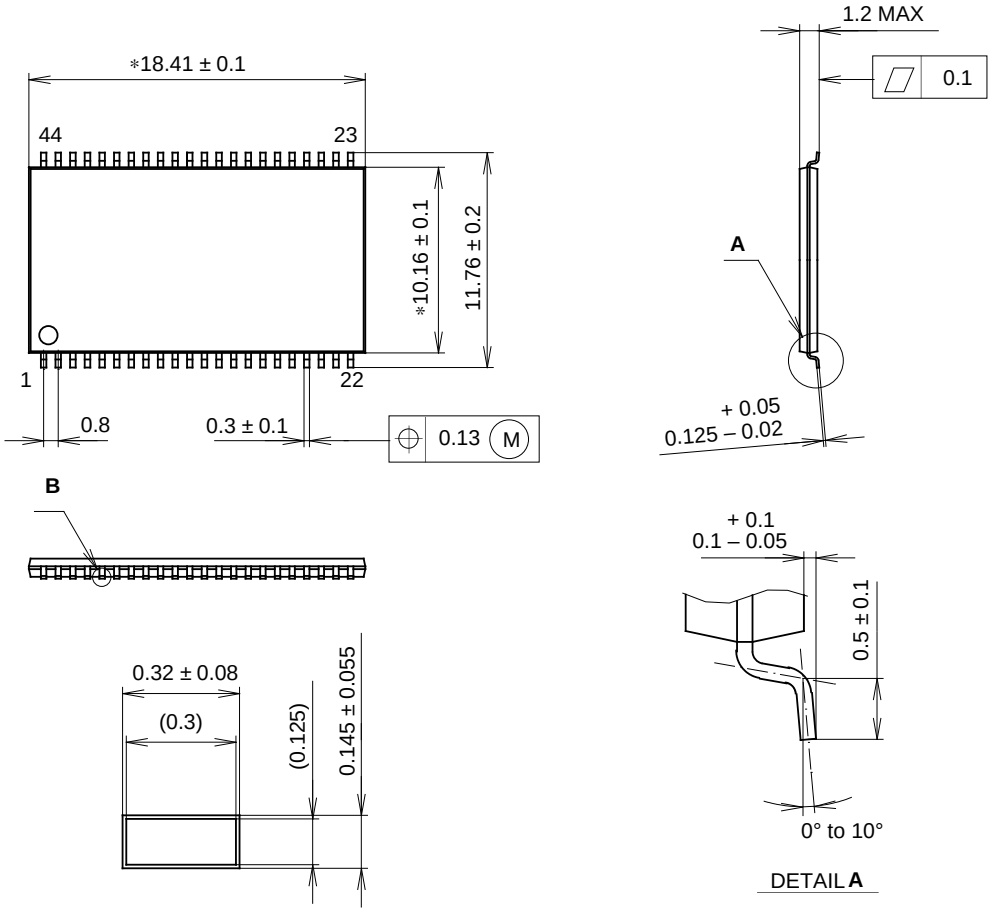
Data Retention Characteristics (Ta = –25 to +85°C)

Item	Symbol	Test condition		Min.	Typ.	Max.	Unit
Data retention voltage	V_{DR}	$\overline{CE} \geq V_{CC} - 0.2V$		2.0	—	3.6	V
Data retention current	I_{CCDR1}	V_{CC} = 3.0V	–25 to +85°C	—	—	24	µA
			–25 to +70°C	—	—	12	
			+25°C	—	0.4	—	
	I_{CCDR2}	V_{CC} = 2.0 to 3.6V		—	0.48*1	28	µA
Data retention setup time	t_{CDRS}	Chip disable to data retention mode		0	—	—	ns
Recovery time	t_R			5	—	—	ms

*1 V_{CC} = 3.3V, Ta = 25°C

Package Outline Unit : mm

44PIN TSOP (II) (PLASTIC) 400mil



DETAIL **B**

DETAIL **A**

NOTE: Dimension "∗" does not include mold protrusion.

SONY CODE	TSOP (II) -44P-L01
EIAJ CODE	TSOP (II) 044-P-0400-A
JEDEC CODE	————

PACKAGE STRUCTURE

MOLDING COMPOUND	EPOXY / PHENOL RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	42 ALLOY
PACKAGE WEIGHT	0.5g